

Low-Cost MEMS Initiators

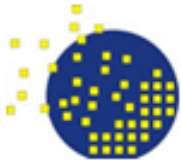
Chopin Hua



MicroAssembly
Technologies, Inc.



Team



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Chopin Hua

Dr. Michael Cohn

Kevin Chang

Brian Kirby

Ross Millenacker



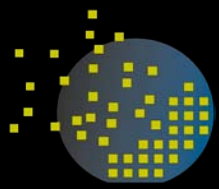
Dr. Brian Fuchs

Anthony DiStasio



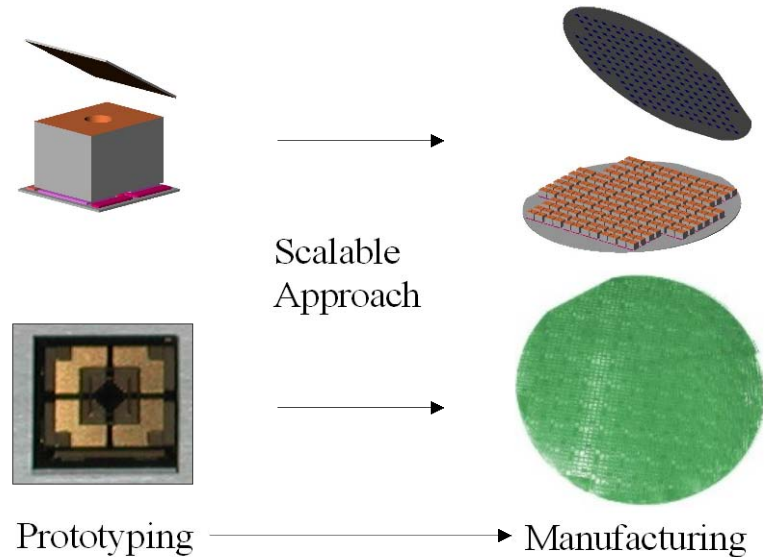
Becki Amendt

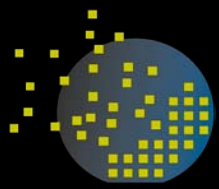
Wayne Hanson



MEMS Background

- Applications beyond Munitions
 - Airbag initiators
 - Stability Control
 - Televisions
- Benefits using MEMS
 - Low cost
 - Reliability
 - More intelligent systems
 - Scalability

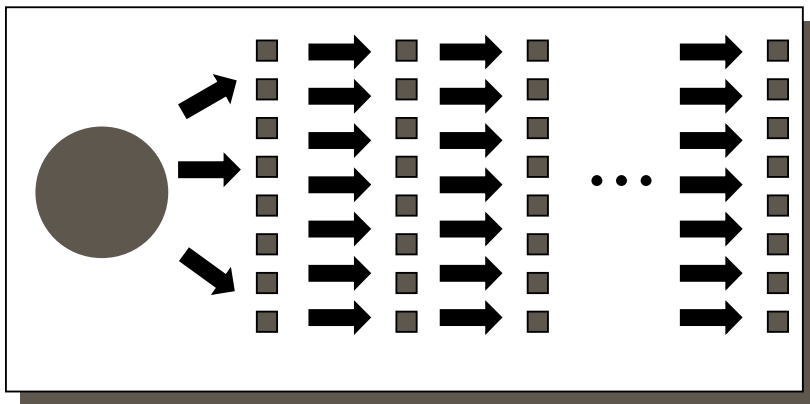




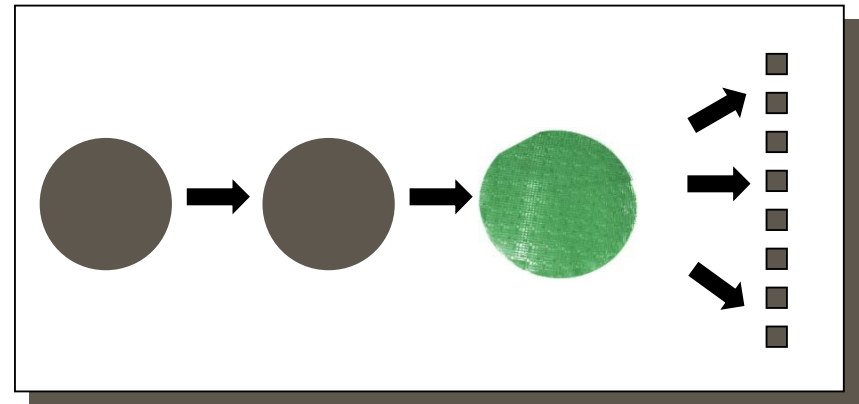
Batch Assembly

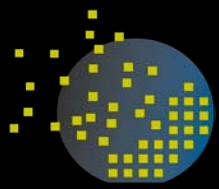
- Assembly/Packaging is Expensive
 - Each Part Must Undergo Many Steps
- Unique Capability
 - One Hundred Steps vs. Tens of Thousands
 - Reduce Cost by >10X

Conventional One-at-a-Time



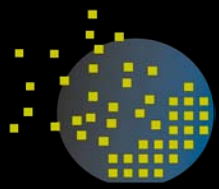
Our Solution: Thousands-at-a Time





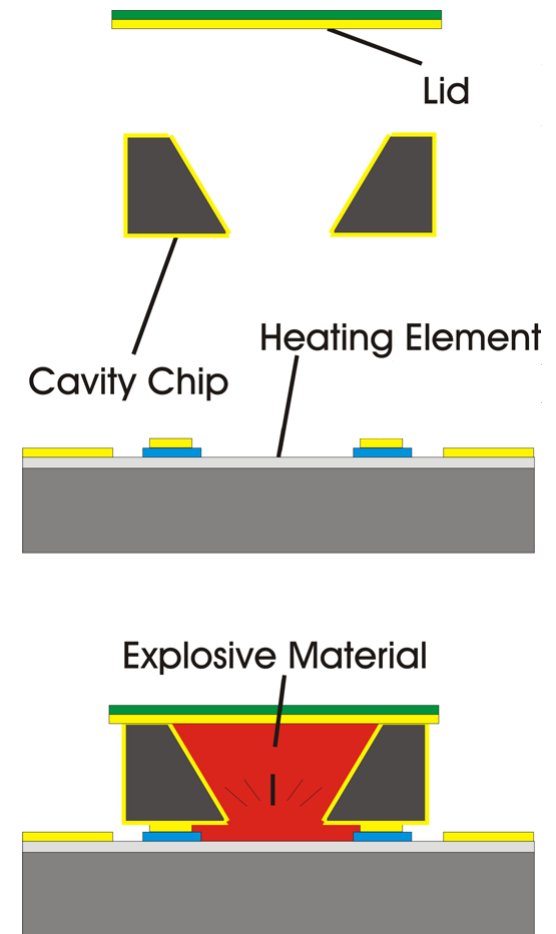
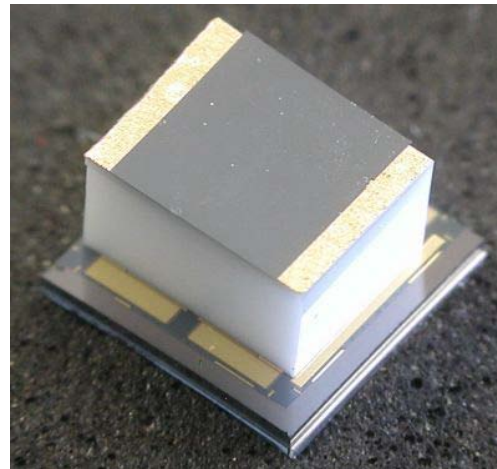
MEMS Initiators

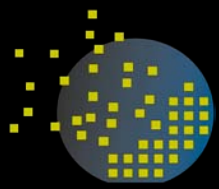
- M100 Drop-In Replacement
 - Batch Processing = Lower Cost, Higher Reliability
 - Commercial Applications
 - Mining, Construction, Oil Drilling
- Silicon Bridge Initiator
 - For Navy IHDIIV S&A devices
 - Applications
 - 40 MM Grenades
 - Mine Countermeasure Dart



Initiators for M100 Replacement

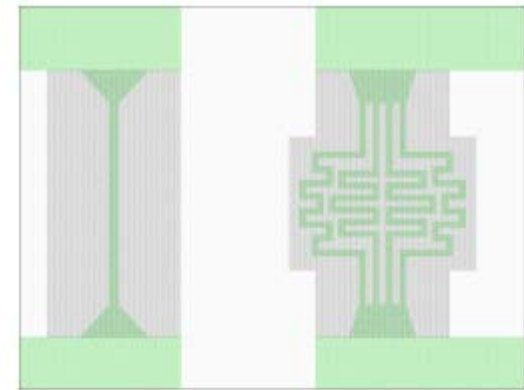
- Three Layer Design
- Tungsten Heating Element
- Batch Processes
 - Fabrication
 - Loading
 - Packaging





1st Generation M100 Replacement

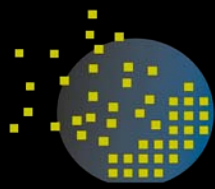
- Pyrex Substrate
- Tungsten Bridgewire
- Fired at 3V off 100 μ F cap
- Pyrex Substrates Pose Process Issues



Heater Devices

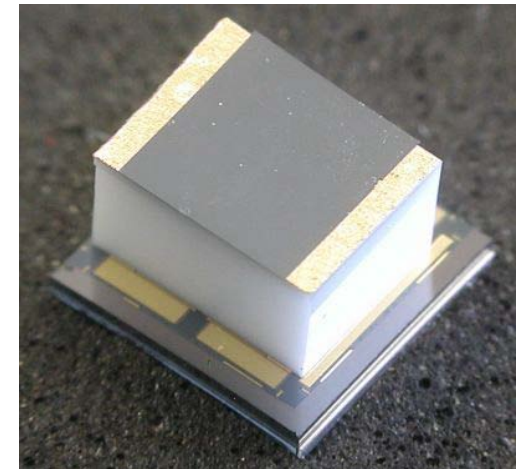
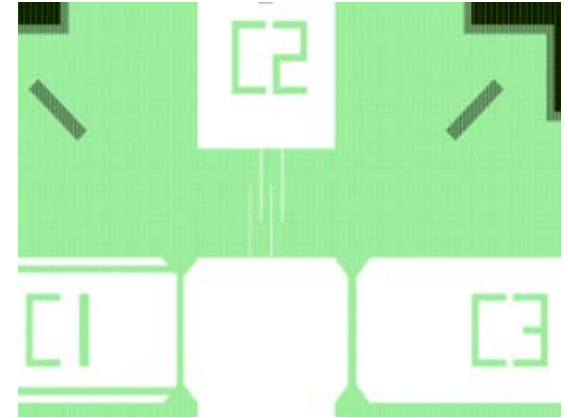


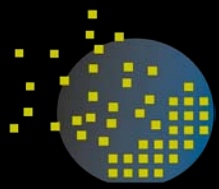
Microdetonator Devices



2nd Generation M100 Replacement

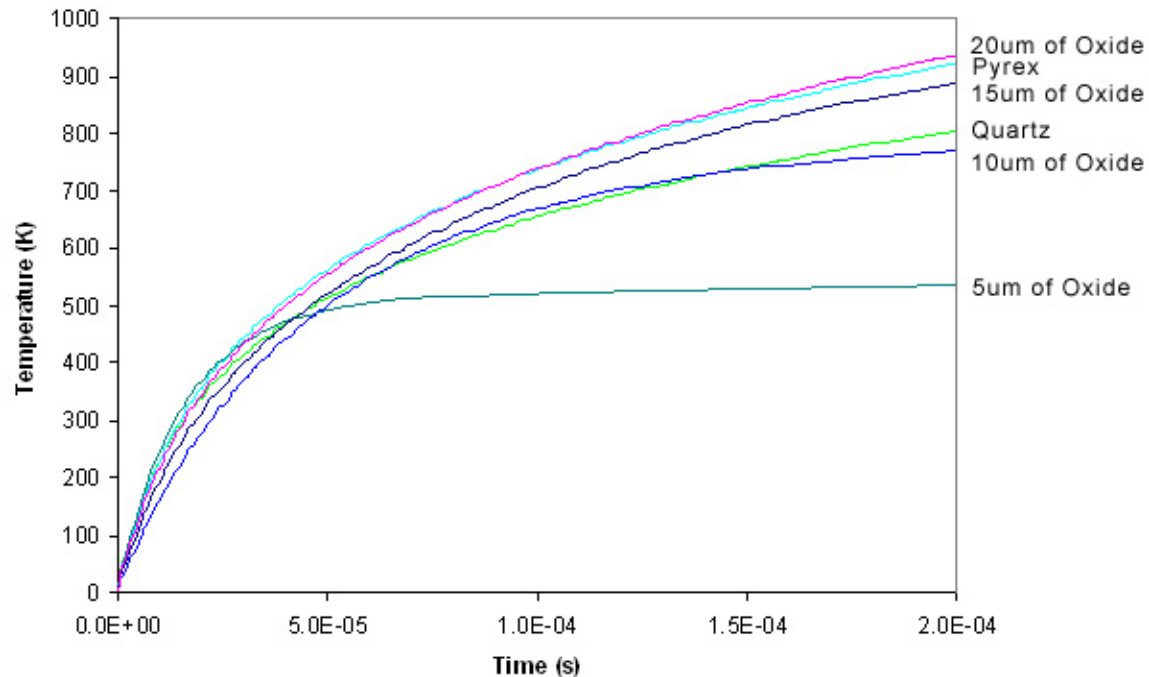
- Pyrex Substrates and Silicon Substrates
- Devices on Pyrex Substrate fired at 3V
- Devices on Silicon Substrate fired at 5V (thermal loss)

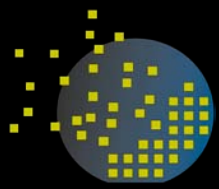




Heater Substrate Modeling

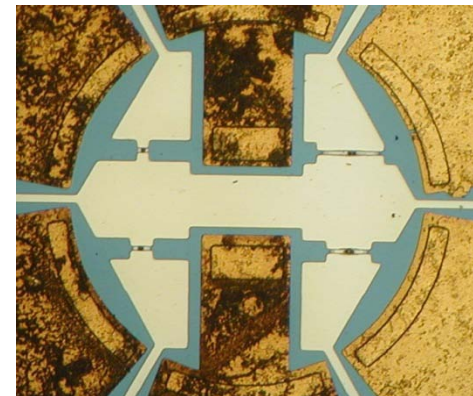
- Silicon with thick oxide layer possible
- Long CVD process is not ideal
- Quartz substrate more cost effective

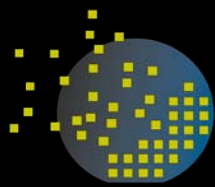




3rd Generation M100 Replacement

- Quartz Substrate
- Lower parasitic resistances
- Higher energy dissipation over bridewire
- Neyer Test on 3rd generation devices
 - 23 devices tested
 - $\mu=1.6088$ V $\sigma=0.0966$ V
 - All-fire at 2.0 V
 - No-fire at 1.2 V

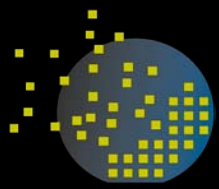




4th Generation M100 Replacement

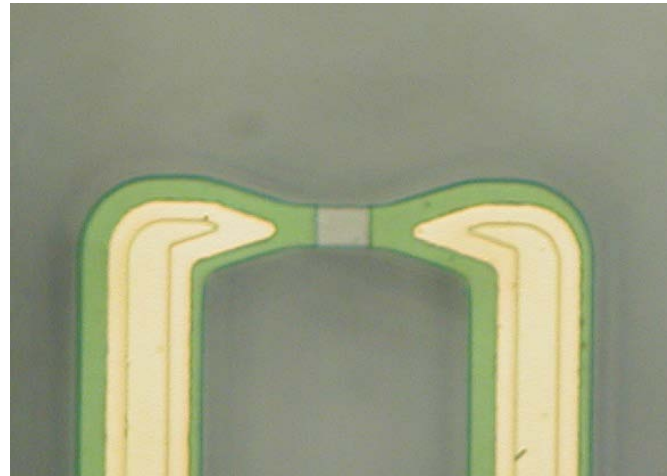
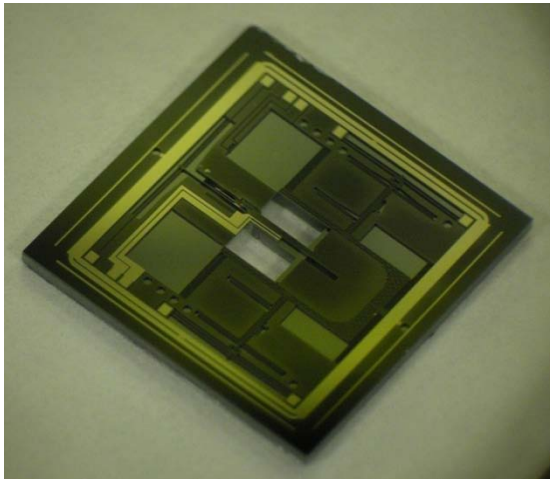
- Lower parasitic resistances
- Higher energy dissipation over bridgewire
- Neyer Test on 4th generation devices
 - 30 devices tested
 - $\mu=1.2097$ V $\sigma=0.0220$ V
 - All-fire at 1.6 V
 - No-fire at 0.7 V
 - Dent into Aluminum: 0.020”

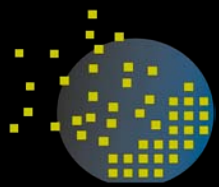




Initiators for S&A Device

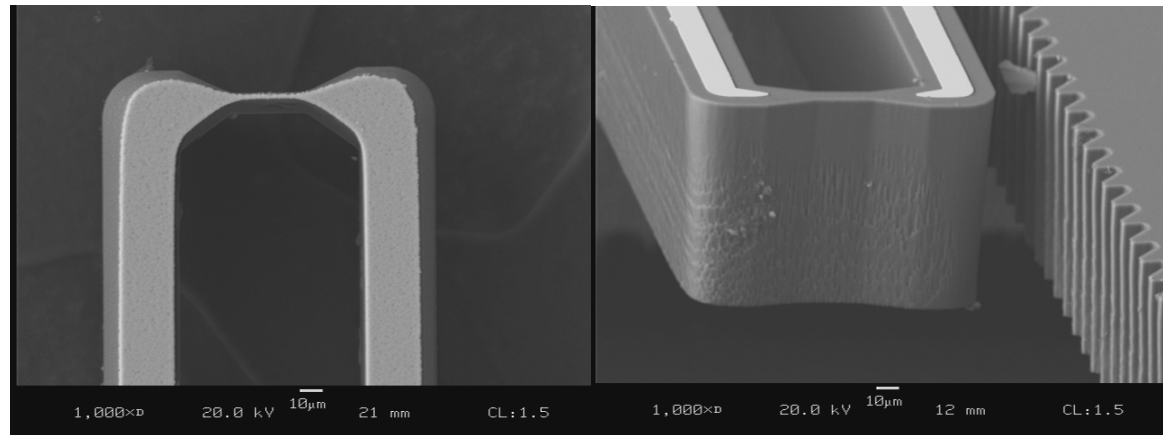
- Navy IHDIIV S&A devices
- SOI MEMS Process for Safe & Arm Device
- Silicon Semiconductor Bridge (SCB) Initiator
- Integrated Initiators Fabricated in Batch Semiconductor Processes

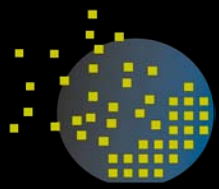




NSWC Silicon Bridge Initiator

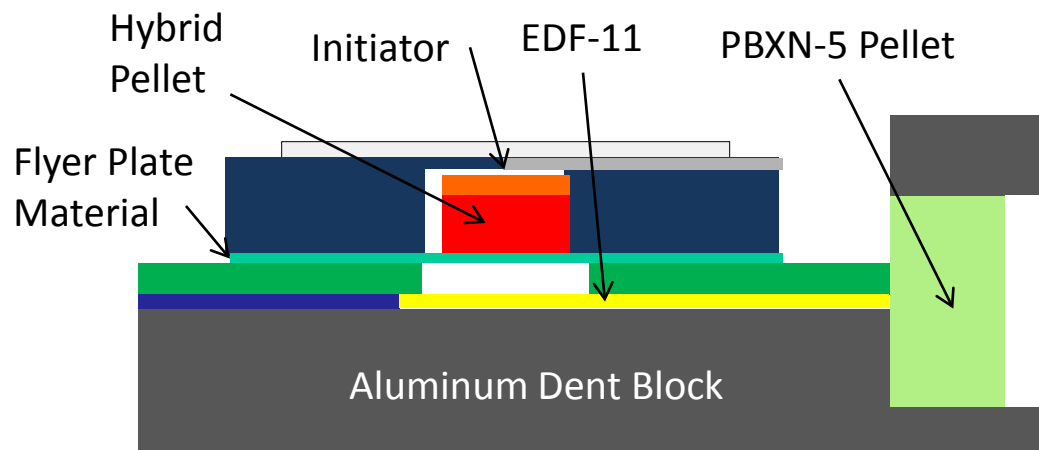
- Composed of a silicon bridge
- Unique geometry used for MEMS S&A device (bridge volume $\sim 20,000 \mu\text{m}^3$, dimensions in the 10's of μm)
- Bursts and forms plasma when voltage is applied
- Plasma crosses air gap (2-5 μm) to initiate primary explosive



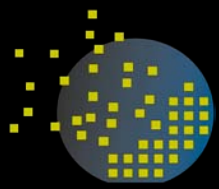


Silicon Bridge Test Setup

- Navy IHDIIV devices
- Explosive train feasibility study with various geometries tested
- Plasma initiates lead styphnate/silver azide pellet
- Sending metal flyer into and initiating EDF-11 strip (12-40 mils thick)
- EDF-11 charge transfers to PBXN-5 pellet

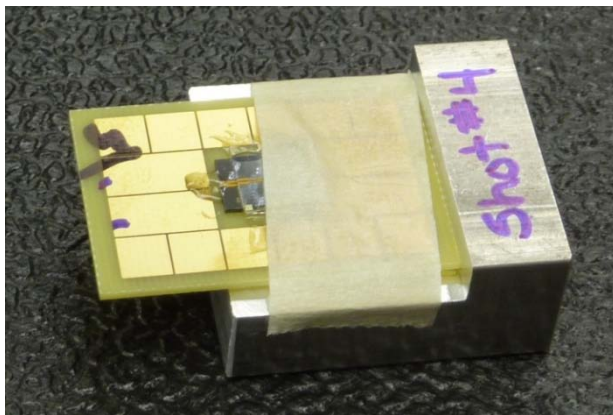


MicroAssembly Technologies



Silicon Bridge Testing

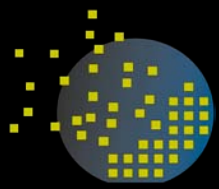
- Flyer successfully initiated thin layer of EDF-11 (15/17 times in various geometries / thicknesses)
- EDF-11 successfully initiated PBXN-5 pellet (4/6 times)
- Dent block analysis underway at NSWC IH



Initiator with Aluminum Dent Block



Dent Block After Successful Charge Transfer



Summary

- **M100 Drop-In Replacement**
 - More Reliable ($\sigma=0.0220$ V)
 - Meets Firing Requirements
 - All-Fire at 1.6 V off 100 μ F cap
 - No-Fire at 0.7 V off 100 μ F cap
- **Silicon Bridge Initiator**
 - Successfully Initiated Explosive Train
 - Semiconductor processing: Firing characteristics can be easily changed per application
 - Fast Acting (μ s range), Low Energy (~ 5 mJ), Very Efficient